

What is claimed is:

1. A semiconductor device comprising:
a wiring pattern and a plurality of dummy patterns
different from the wiring pattern; and
an insulating film formed on the wiring pattern and
the dummy patterns by a chemical vapor deposition method
and planarized by CMP,
wherein the dummy patterns are provided with
pattern non-forming regions each having a width filled by
plus sizing of the insulating film upon formation of the
insulating film.
2. A semiconductor device according to claim 1,
wherein the pattern non-forming regions of the dummy
patterns are formed in stripe form.
3. A semiconductor device according to claim 1,
wherein the pattern non-forming regions of the dummy
patterns are formed in character or graphical form.
4. A semiconductor device according to claim 1,
wherein the pattern non-forming regions of the dummy
patterns are shaped in character or graphical forms
different every said dummy patterns.
5. A semiconductor device according to claim 1,

wherein the dummy patterns are square.

6. A semiconductor device according to claim 1,
wherein the dummy patterns are arranged in lattice form.